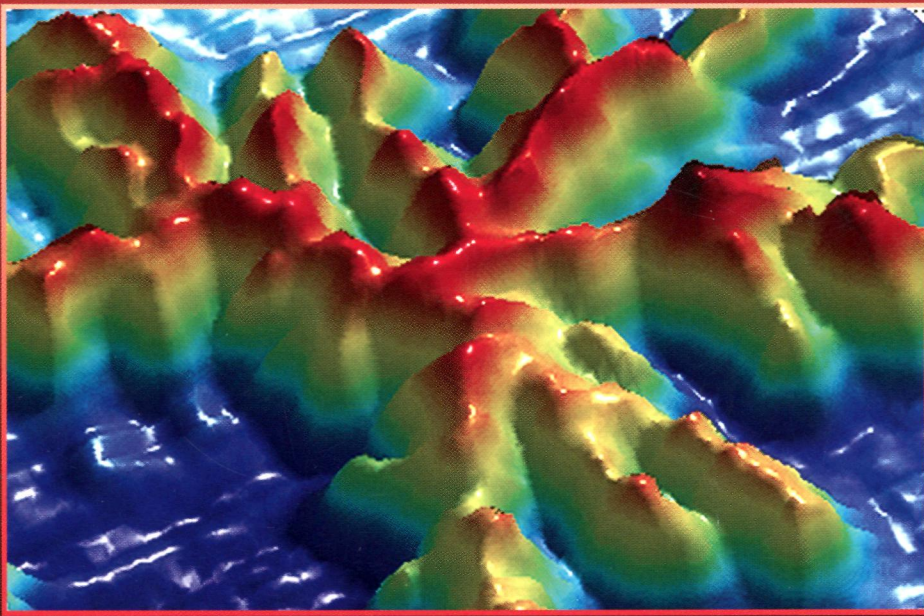


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# JVSTB

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## Nanotechnology and Microelectronics: Materials, Processing, Measurement, and Phenomena



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### Special Issue on High-k Dielectrics



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## Nanotechnology and Microelectronics:

## Materials, Processing, Measurement, and Phenomena

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